



# **NPN General Purpose Amplifier**

This device is for use as a medium power amplifier and switch requiring collector currents up to 500 mA. Sourced from Process 19. See PN2222A for characteristics.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	40	V
V <sub>CBO</sub>	Collector-Base Voltage	75	V
V <sub>EBO</sub>	Emitter-Base Voltage	6.0	V
I <sub>C</sub>	Collector Current - Continuous	1.0	А
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

# Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		TN2219A	
P <sub>D</sub>	Total Device Dissipation	1.0	W
	Derate above 25°C	8.0	W/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	50	°C/W

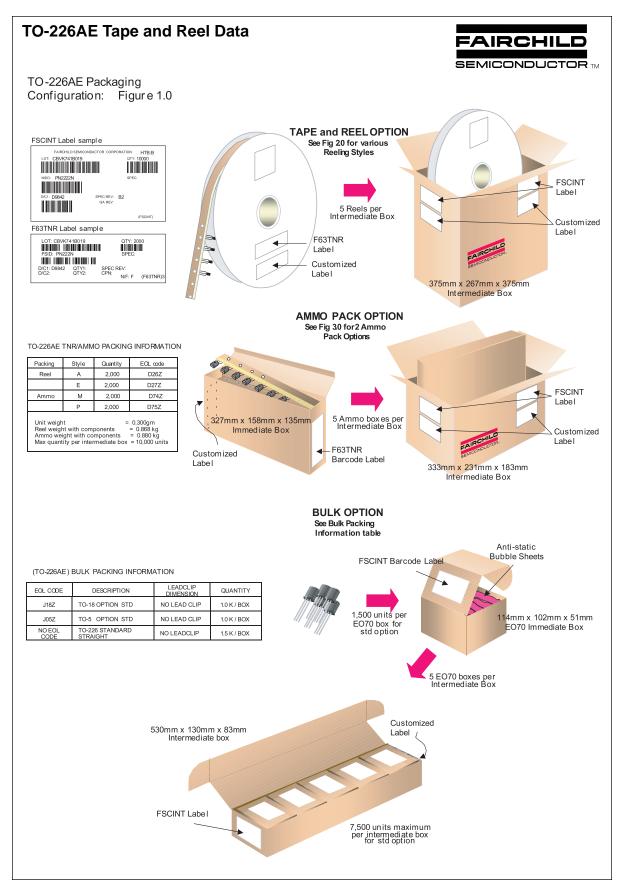
<sup>1)</sup> These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# NPN General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10  \text{mA}, I_{\rm B} = 0$	40		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = 10 \mu\text{A}, I_{E} = 0$	75		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{E} = 10 \mu\text{A}, I_{C} = 0$	6.0		V
	Collector Cutoff Current	$V_{CE} = 60 \text{ V}, V_{EB(OFF)} = 3.0 \text{ V}$	0.0	10	nA
I <sub>CEX</sub>	Collector Cutoff Current	$V_{CB} = 60 \text{ V}, V_{EB(OFF)} = 3.0 \text{ V}$ $V_{CB} = 60 \text{ V}, I_{E} = 0$		10	nA
СВО	Collector Cuton Current	$V_{CB} = 60 \text{ V}, I_E = 0$ $V_{CB} = 60 \text{ V}, I_E = 0, T_A = 150^{\circ}\text{C}$		10	μA
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_{C} = 0$		10	nΑ
I <sub>BL</sub>	Base Cutoff Current	$V_{CE} = 60 \text{ V}, V_{EB(OFF)} = 3.0$		20	nA
		$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 150 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 150 \text{ mA}, V_{CE} = 1.0 \text{ V}$	50 75 100 50	300	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage*	$I_C = 500 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	40	0.3 1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage*	$I_C$ = 150 mA, $I_B$ = 1.0 mA $I_C$ = 500 mA, $I_B$ = 5.0 mA	0.6	1.2 2.0	V
ONANII CI					
SIVIALL SI	GNAL CHARACTERISTICS				
	GNAL CHARACTERISTICS Output Capacitance	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 100 kHz		8.0	pF
C <sub>obo</sub>		$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 100 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, I_{C} = 0, f = 100 \text{ kHz}$		8.0 25	pF pF
C <sub>obo</sub>	Output Capacitance	$V_{EB} = 0.5 \text{ V}, I_{C} = 0, f = 100 \text{ kHz}$ $I_{C} = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}, f = 1.0 \text{ kHz}$	50 75		
C <sub>obo</sub> C <sub>ibo</sub> h <sub>fe</sub>	Output Capacitance Input Capacitance	$V_{EB} = 0.5 \text{ V}, I_{C} = 0, f = 100 \text{ kHz}$		25 300	
C <sub>obo</sub> C <sub>ibo</sub> h <sub>fe</sub>	Output Capacitance Input Capacitance Small-Signal Current Gain	$\begin{split} V_{EB} &= 0.5 \text{ V},  I_{C} = 0,  f = 100 \text{ kHz} \\ I_{C} &= 1.0 \text{ mA},  V_{CE} = 10 \text{ V},  f = 1.0 \text{ kHz} \\ I_{C} &= 10 \text{ mA},  V_{CE} = 10 \text{ V},  f = 1.0 \text{ kHz} \\ I_{E} &= 20 \text{ mA},  V_{CB} = 20 \text{ V},  f = 31.8 \text{ MHz} \\ I_{C} &= 100  \mu\text{A},  V_{CE} = 10 \text{ V},  R_{S} = 1.0 \text{ k}\Omega \end{split}$		25 300 375	pF
Cobo Cibo Ofe Pb'Cc	Output Capacitance Input Capacitance Small-Signal Current Gain Collector Base Time Constant	$\begin{split} V_{EB} &= 0.5 \text{ V},  I_{C} = 0,  f = 100 \text{ kHz} \\ I_{C} &= 1.0 \text{ mA},  V_{CE} = 10 \text{ V},  f = 1.0 \text{ kHz} \\ I_{C} &= 10 \text{ mA},  V_{CE} = 10 \text{ V},  f = 1.0 \text{ kHz} \\ I_{E} &= 20 \text{ mA},  V_{CB} = 20 \text{ V},  f = 31.8 \text{ MHz} \end{split}$		25 300 375 150	pF pS
C <sub>obo</sub> Cibo  nfe  rb'C <sub>C</sub> NF  Re(h <sub>ie</sub> )	Output Capacitance Input Capacitance Small-Signal Current Gain Collector Base Time Constant Noise Figure Real Part of Common-Emitter	$\begin{split} &V_{EB} = 0.5 \text{ V}, \ I_{C} = 0, \ f = 100 \text{ kHz} \\ &I_{C} = 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \ f = 1.0 \text{ kHz} \\ &I_{C} = 10 \text{ mA}, \ V_{CE} = 10 \text{ V}, \ f = 1.0 \text{ kHz} \\ &I_{E} = 20 \text{ mA}, \ V_{CB} = 20 \text{ V}, \ f = 31.8 \text{ MHz} \\ &I_{C} = 100 \mu\text{A}, \ V_{CE} = 10 \text{ V}, \ R_{S} = 1.0 \text{ k}\Omega \\ &f = 1.0 \text{ kHz}, \ B_{W} = 1.0 \text{ kHz} \\ &I_{C} = 20 \text{ mA}, \ V_{CE} = 20 \text{ V}, \end{split}$		25 300 375 150 4.0	pF pS dB
C <sub>obo</sub> C <sub>ibo</sub> hfe rb'C <sub>C</sub> NF Re(h <sub>ie</sub> )	Output Capacitance Input Capacitance Small-Signal Current Gain Collector Base Time Constant Noise Figure Real Part of Common-Emitter High Frequency Input Impedance	$\begin{split} &V_{EB} = 0.5 \text{ V}, \ I_{C} = 0, \ f = 100 \text{ kHz} \\ &I_{C} = 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \ f = 1.0 \text{ kHz} \\ &I_{C} = 10 \text{ mA}, \ V_{CE} = 10 \text{ V}, \ f = 1.0 \text{ kHz} \\ &I_{E} = 20 \text{ mA}, \ V_{CB} = 20 \text{ V}, \ f = 31.8 \text{ MHz} \\ &I_{C} = 100 \mu\text{A}, \ V_{CE} = 10 \text{ V}, \ R_{S} = 1.0 \text{ k}\Omega \\ &f = 1.0 \text{ kHz}, \ B_{W} = 1.0 \text{ kHz} \\ &I_{C} = 20 \text{ mA}, \ V_{CE} = 20 \text{ V}, \end{split}$		25 300 375 150 4.0	pF pS dB
C <sub>obo</sub> C <sub>ibo</sub> h <sub>fe</sub> rb'C <sub>C</sub> NF Re(h <sub>ie</sub> )	Output Capacitance Input Capacitance Small-Signal Current Gain Collector Base Time Constant Noise Figure Real Part of Common-Emitter High Frequency Input Impedance	$\begin{split} V_{EB} &= 0.5 \text{ V}, \ I_C = 0, \ f = 100 \text{ kHz} \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \ f = 1.0 \text{ kHz} \\ I_C &= 10 \text{ mA}, \ V_{CE} = 10 \text{ V}, \ f = 1.0 \text{ kHz} \\ I_E &= 20 \text{ mA}, \ V_{CB} = 20 \text{ V}, \ f = 31.8 \text{ MHz} \\ I_C &= 100 \text{ \muA}, \ V_{CE} = 10 \text{ V}, \ R_S = 1.0 \text{ k}\Omega \\ f &= 1.0 \text{ kHz}, \ B_W = 1.0 \text{ kHz} \\ I_C &= 20 \text{ mA}, \ V_{CE} = 20 \text{ V}, \\ f &= 300 \text{ MHz} \\ \end{split}$		25 300 375 150 4.0	pF pS dB
Cobo Cibo hfe rb'Cc NF Re(hie)	Output Capacitance Input Capacitance Small-Signal Current Gain Collector Base Time Constant Noise Figure Real Part of Common-Emitter High Frequency Input Impedance NG CHARACTERISTICS Delay Time	$\begin{split} V_{EB} &= 0.5 \text{ V},  I_{C} = 0,  f = 100 \text{ kHz} \\ I_{C} &= 1.0 \text{ mA},  V_{CE} = 10 \text{ V},  f = 1.0 \text{ kHz} \\ I_{C} &= 10 \text{ mA},  V_{CE} = 10 \text{ V},  f = 1.0 \text{ kHz} \\ I_{E} &= 20 \text{ mA},  V_{CB} = 20 \text{ V},  f = 31.8 \text{ MHz} \\ I_{C} &= 100  \mu\text{A},  V_{CE} = 10 \text{ V},  R_{S} = 1.0 \text{ k}\Omega \\ f &= 1.0 \text{ kHz},  B_{W} = 1.0 \text{ kHz} \\ I_{C} &= 20 \text{ mA},  V_{CE} = 20 \text{ V}, \\ f &= 300 \text{ MHz} \end{split}$		25 300 375 150 4.0 60	pF pS dB Ω

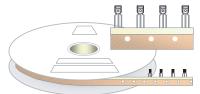
<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%



# **TO-226AE Tape and Reel Data, continued**

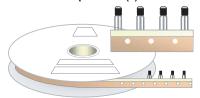
**TO-226AE Reeling Style** Configuration: Figure 2.0

## Machine Option "A" (H)



Style "A" D26Z, D70Z (s/h)

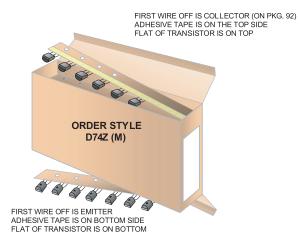
### Machine Option "E"(J)



Style "E" D27Z, D71Z (s/h)

# **TO-226AE Radial Ammo Packaging**

Configuration: Figure 3.0



FIRST WIRE OFF IS EMITTER (ON PKG. 92) ADHESIVE TAPE IS ON THE TOP SIDE FLAT OF TRANSISTOR IS ON BOTTOM



FLAT OF TRANSISTOR IS ON TOP

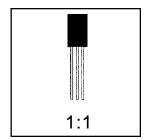
#### **TO-226AE Tape and Reel Data, continued** TO-226AE Tape and Reel Taping Dimension Configuration: Figure 4.0 ITEM DESCRIPTION SYMBOL DIMENSION Base of Package to Lead Bend 0.098 (max) Component Height Hb 1.078 (+/- 0.050) User Direction of Feed 0.630 (+/- 0.020) Lead Clinch Height НΩ Component Base Height H1 0.748 (+/- 0.020) Component Alignment (side/side) Pd 0.040 (max) 0.031 (max) Component Alignment ( front/back ) Hd 0.500 (+/- 0.020) Component Pitch РО Feed Hole Pitch 0.500 (+/- 0.008) Hole Center to First Lead P1 0.150 (+0.009, -0.010) Hole Center to Component Center P2 0.247 (+/- 0.007) Lead Spread F1/F2 0.104 (+/- 0 010) Lead Thickness d 0.018 (+0.002, -0.003) 0.429 (max) Out Lead Length Taped Lead Length 0.209 (+0.051, -0.052) L1 Taped Lead Thickness 0.032 (+/- 0.006) Carrier Tape Thickness t1 0.021 (+/- 0.006) TO-226AE Reel Carrier Tape Width 0.708 (+0.020, -0.019) W Configuration: Figure 5.0 Hold - down Tape Width wo 0.236 (+/- 0.012) 0.035 (max) Hold - down Tape position W1 0.360 (+/- 0.025) Feed Hole Position W2 0.157 (+0.008, -0.007) Sprocket Hole Diameter DO 0.004 (max) Lead Spring Out S Note: All dmensions are in inches. D4 ITEM DESCRIPTION SYMBOL MINIMUM MAXIMUM Red Diameter 13975 14025 Arbor Hole Diameter (Standard) 1.200 D2 1.160 D2 0.650 0.700 (Small Hole) Core Diameter D3 3.100 3.300 Hub Recess Inner Diameter 3.100 D4 Hub Recess Depth W 1 0.370 0.570 Range to Range Inner Width W2 1.630 1.690 Hub to Hub Center Width 2.090 WЗ Note: All dimensions are inches

# **TO-226AE Package Dimensions**



# TO-226AE (FS PKG Code 95, 99)





Scale 1:1 on letter size paper

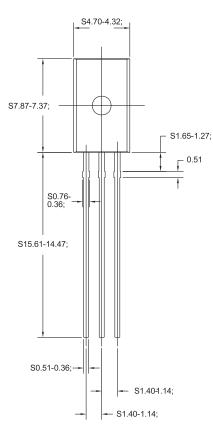
Dimensions shown below are in: inches [millimeters]

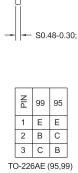
Part Weight per unit (gram): 0.300

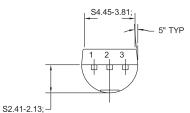
- S1.52-1.02;

S7.73-7.10;

2" TYP







For leadformed option ordering, refer to Tape & Reel data information.

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DOME™ Quiet Series™ ISOPLANAR™ E<sup>2</sup>CMOS<sup>TM</sup> MICROWIRE™ SILENT SWITCHER® EnSigna™ **OPTOLOGIC™** SMART START™ FACT™ **OPTOPLANAR™** SuperSOT™-3 FACT Quiet Series™ PACMAN™ SuperSOT™-6 **РОР**ТМ SuperSOT™-8 FAST®

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